

## LETTERS

### **Reproducible nanostructure fabrication using atomic force microscopy indentation with minimal tip damage**

SeungHee Jeon, BongWoo Ryu, Wonho Jhe, Zheong G. Khim and Byung I. Kim  
J. Vac. Sci. Technol. B **32**, 020601 (2014); <http://dx.doi.org/10.1116/1.4862538>

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### **Selective deposition of graphene sheets on a flexible substrate by a nonuniform electric field**

Sooyeon Oh, Hyunik Park, Younghun Jung, Jihyun Kim, Jiwan Kim and Min Suk Oh  
J. Vac. Sci. Technol. B **32**, 020602 (2014); <http://dx.doi.org/10.1116/1.4862536>

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### **Asymmetric resistive switching characteristics of $\text{In}_2\text{O}_3:\text{SiO}_2$ cosputtered thin film memories**

Wei-Kang Hsieh, Kin-Tak Lam and Shou-Jinn Chang  
J. Vac. Sci. Technol. B **32**, 020603 (2014); <http://dx.doi.org/10.1116/1.4863915>

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### **Novel high-throughput and maskless photolithography to fabricate plasmonic molecules**

Aireza Bonakdar, Sung Jun Jang and Hooman Mohseni  
J. Vac. Sci. Technol. B **32**, 020604 (2014); <http://dx.doi.org/10.1116/1.4865999>

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### **Quality of development of latent sebaceous fingerprints coated with thin films of different morphologies**

Stephen E. Swiontek, Drew P. Pulsifer and Akhlesh Lakhtakia  
J. Vac. Sci. Technol. B **32**, 020605 (2014); <http://dx.doi.org/10.1116/1.4867440>

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## REVIEW ARTICLES

### **Helium ion microscopy**

Gregor Hlawacek, Vasilisa Veligura, Raoul van Gastel and Bene Poelsema  
J. Vac. Sci. Technol. B **32**, 020801 (2014); <http://dx.doi.org/10.1116/1.4863676>

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### **Heusler nanoparticles for spintronics and ferromagnetic shape memory alloys**

Changhai Wang, Judith Meyer, Niclas Teichert, Alexander Auge, Elisabeth Rausch, Benjamin Balke, Andreas Hütten, Gerhard H. Fecher and Claudia Felser  
J. Vac. Sci. Technol. B **32**, 020802 (2014); <http://dx.doi.org/10.1116/1.4866418>

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## ELECTRONIC & OPTOELECTRONIC MATERIALS, DEVICES & PROCESSING

### **Void-free direct bonding of InP to Si: Advantages of low H-content and ozone activation**

A. Itawi, K. Pantzas, I. Sagnes, G. Patriarche and A. Talneau

J. Vac. Sci. Technol. B **32**, 021201 (2014); <http://dx.doi.org/10.1116/1.4863317>

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### **Development of diamond cathode materials for enhancing the electron field emission and plasma characteristics using two-step microwave plasma enhanced chemical vapor deposition process**

Shiu-Cheng Lou, Chulung Chen, Srinivasu Kunuku, Keh-Chyang Leou, Chi-Young Lee, Huang-Chin Chen and I-Nan Lin

J. Vac. Sci. Technol. B **32**, 021202 (2014); <http://dx.doi.org/10.1116/1.4864067>

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### **Enhancement of AlGaN/GaN high electron mobility transistors off-state drain breakdown voltage via backside proton irradiation**

Shun Li, Ya-Hsi Hwang, Yueh-Ling Hsieh, Lei Lei, Fan Ren, Stephen J. Pearton, Erin Patrick, Mark E. Law, Camilo Velez Cuervo and David. J. Smith

J. Vac. Sci. Technol. B **32**, 021203 (2014); <http://dx.doi.org/10.1116/1.4864070>

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### **Top-down fabrication of large-area GaN micro- and nanopillars**

Ratan Debnath, Jong-Yoon Ha, Baomei Wen, Dipak Paramanik, Abhishek Motayed, Matthew R. King and Albert V. Davydov

J. Vac. Sci. Technol. B **32**, 021204 (2014); <http://dx.doi.org/10.1116/1.4865908>

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### **Two-terminal vertical memory cell for cross-point static random access memory applications**

Xiaodong Tong, Jun Luo, Hao Wu, Qingqing Liang, Huicai Zhong, Hui long Zhu and Chao Zhao

J. Vac. Sci. Technol. B **32**, 021205 (2014); <http://dx.doi.org/10.1116/1.4865572>

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### **Structural and optical properties of $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ high electron mobility transistor structures grown on 200 mm diameter Si(111) substrates**

Thirumaleshwara N. Bhat, Surani B. Dolmanan, Yilmaz Dikme, Hui R. Tan, Lakshmi K. Bera and Sudhiranjan Tripathy

J. Vac. Sci. Technol. B **32**, 021206 (2014); <http://dx.doi.org/10.1116/1.4866429>

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### **Inductively coupled plasma reactive ion etching of GaAs wafer pieces with enhanced device yield**

Michael K. Connors, Leo J. Missaggia, William S. Spencer and George W. Turner

J. Vac. Sci. Technol. B **32**, 021207 (2014); <http://dx.doi.org/10.1116/1.4867356>

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## LITHOGRAPHY

### **Polymethyl methacrylate/hydrogen silsesquioxane bilayer resist electron beam lithography process for etching 25 nm wide magnetic wires**

Jean Anne Curivan, Saima Siddiqui, Sungmin Ahn, Larysa Tryputen, Geoffrey S. D. Beach, Marc A. Baldo and Caroline A. Ross

J. Vac. Sci. Technol. B **32**, 021601 (2014); <http://dx.doi.org/10.1116/1.4867753>

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### **Focused helium and neon ion beam induced etching for advanced extreme ultraviolet lithography mask repair**

Carlos M. Gonzalez, Rajendra Timilsina, Guoliang Li, Gerd Duscher, Philip D. Rack, Winand Slingenbergh, Willem F. van Dorp, Jeff T. M. De Hosson, Kate L. Klein, Huimeng M. Wu and Lewis A. Stern

J. Vac. Sci. Technol. B **32**, 021602 (2014); <http://dx.doi.org/10.1116/1.4868027>

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## NANOMETER SCIENCE & TECHNOLOGY

### **Nanostructuring of GaAs with tailored topologies using colloidal lithography and dry etching**

Kashif Masud Awan, Reza Sanatinia and Srinivasan Anand

J. Vac. Sci. Technol. B **32**, 021801 (2014); <http://dx.doi.org/10.1116/1.4862976>

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### **Dewetting of Au/Ni bilayer films on prepatterned substrates and the formation of arrays of supersaturated Au-Ni nanoparticles**

Andreas Herz, Dong Wang and Peter Schaa

J. Vac. Sci. Technol. B **32**, 021802 (2014); <http://dx.doi.org/10.1116/1.4863320>

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### **Impedance characterization of nanogap interdigitated electrode arrays fabricated by tilted angle evaporation for electrochemical biosensor applications**

Dae-Young Jeon, So Jeong Park, Yongha Kim, Min-Ju Shin, Pil Soo Kang and Gyu-Tae Kim

J. Vac. Sci. Technol. B **32**, 021803 (2014); <http://dx.doi.org/10.1116/1.4863512>

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### **Measurement of periodicity and strain in arrays of single crystal silicon and pseudomorphic $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ fin structures using x-ray reciprocal space maps**

Manasa Medikonda, Gangadhara R. Muthinti, Jody Fronheiser, Vimal Kamineni, Matthew Wormington, Kevin Matney, Thomas N. Adam, Evguenia Karapetrova and Alain C. Diebold



## NANOMETER SCIENCE & TECHNOLOGY

### **Spurious dangling bond formation during atomically precise hydrogen depassivation lithography on Si(100): The role of liberated hydrogen**

Joshua B. Ballard, James H. G. Owen, Justin D. Alexander, William R. Owen, Ehud Fuchs, John N. Randall, Roberto C. Longo and Kyeongjae Cho  
J. Vac. Sci. Technol. B **32**, 021805 (2014); <http://dx.doi.org/10.1116/1.4864302>

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### **Patterning of silicon nitride for CMOS gate spacer technology. II. Impact of subsilicon surface carbon implantation on epitaxial regrowth**

Romuald Blanc, Cécile Jenny, Sébastien Lagrasta, François Leverd and Olivier Joubert  
J. Vac. Sci. Technol. B **32**, 021806 (2014); <http://dx.doi.org/10.1116/1.4865896>

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### **Patterning of silicon nitride for CMOS gate spacer technology. III. Investigation of synchronously pulsed CH<sub>3</sub>F/O<sub>2</sub>/He plasmas**

Romuald Blanc, François Leverd, Maxime Darnon, Gilles Cunge, Sylvain David and Olivier Joubert  
J. Vac. Sci. Technol. B **32**, 021807 (2014); <http://dx.doi.org/10.1116/1.4867357>

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### **Enhanced field emission from hydrogenated SnO<sub>2</sub> nanoparticles embedded in TiO<sub>2</sub> film on fluorinated tin oxide substrate**

Xu-Qiang Zhang, Jian-Biao Chen, Wei-Dong Zhu and Cheng-Wei Wang  
J. Vac. Sci. Technol. B **32**, 021808 (2014); <http://dx.doi.org/10.1116/1.4867885>

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### **Fabrication of polymer antireflection structures by injection molding using ordered anodic porous alumina mold**

Takashi Yanagishta, Mikio Masui, Naoto Ikegawa and Hideki Masuda  
J. Vac. Sci. Technol. B **32**, 021809 (2014); <http://dx.doi.org/10.1116/1.4868030>

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## MICROELECTRONIC & NANO ELECTRONIC DEVICES

### **Theoretical and practical approach to overcome curvature radius limitation of conductive atomic force microscopy tip for imaging of advanced technological node static random access memory devices**

Tsu Hau Ng, Sabintha James, Mohammed Khalid Bin Dawood, Hao Tan, Yamin Huang, Pariyarathu Salimon Limin, Pik Kee Tan, Jeffrey Chor Keung Lam and Zhihong Mai  
J. Vac. Sci. Technol. B **32**, 022201 (2014); <http://dx.doi.org/10.1116/1.4863962>

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### **Study on the effects of proton irradiation on the dc characteristics of AlGaN/GaN high**

**electron mobility transistors with source field plate**

Lu Liu, Ya-Hsi Hwang, Yuyin Xi, Fan Ren, Valentin Craciun, Stephen J. Pearton, Gwangseok Yang, Hong-Yeol Kim and Jihyun Kim  
J. Vac. Sci. Technol. B **32**, 022202 (2014); <http://dx.doi.org/10.1116/1.4866401>

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**Systematic procedure to optimize chamber seasoning conditions with optical emission spectroscopy in plasma etching**

Kye Hyun Baek, Sang Wook Park, Geum Jung Seong, Gyung Jin Min, Gilhyeon Choi, Ho-Kyu Kang, Eun Seung Jung, Chonghun Han and Thomas F. Edgar  
J. Vac. Sci. Technol. B **32**, 022203 (2014); <http://dx.doi.org/10.1116/1.4865909>

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**Contamination mitigation of hydrogen silsesquioxane resist processed with Na<sup>+</sup>-containing developer for nanoscale CMOS device patterning**

Markus Brink, Isaac Lauer, Sebastian U. Engelmann, Amlan Majumdar, Stephan A. Cohen, Ernst Kratschmer and Michael A. Guillorn  
J. Vac. Sci. Technol. B **32**, 022204 (2014); <http://dx.doi.org/10.1116/1.4867653>

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**26TH INTERNATIONAL VACUUM NANO ELECTRONICS CONFERENCE (26TH IVNC 2013)****Field emission study of change in work function of poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) film**

Ying Jie Xing, Min Fang Qian, Jing Fang Qin and Geng Min Zhang  
J. Vac. Sci. Technol. B **32**, 02B101 (2014); <http://dx.doi.org/10.1116/1.4827635>

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**Synthesis of cubic boron nitride films on Si tips via chemical vapor deposition and the field emission properties**

Masanori Kobayashi, Hidetoshi Miyashita, Naoki Inomata and Takahito Ono  
J. Vac. Sci. Technol. B **32**, 02B102 (2014); <http://dx.doi.org/10.1116/1.4843075>

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**Picosecond electrical switching of single-gate metal nanotip arrays**

Soichiro Tsujino and Martin Paraliev  
J. Vac. Sci. Technol. B **32**, 02B103 (2014); <http://dx.doi.org/10.1116/1.4838295>

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**Influence of the emitted electron energy distribution from nanocathodes upon the current-voltage characteristics**

Anatoliy Evtukh, Anton Grygoriev, Volodymyr Litovchenko, Olga Steblova, Oktay Yilmazoglu, Hans L. Hartnagel and Hidenori Mimura  
J. Vac. Sci. Technol. B **32**, 02B104 (2014); <http://dx.doi.org/10.1116/1.4843715>

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**CMOS field emission devices based on {111} silicon surfaces**

Michael Bachmann, Andreas Pahlke, Carolin Axt, Bastian Hinze and Walter Hansch  
J. Vac. Sci. Technol. B **32**, 02B105 (2014); <http://dx.doi.org/10.1116/1.4860953>

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**HfC(310) high brightness sources for advanced imaging applications**

William A. Mackie, Josh M. Lovell, Todd W. Curtis and Gerald G. Magera  
J. Vac. Sci. Technol. B **32**, 02B106 (2014); <http://dx.doi.org/10.1116/1.4862444>

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**Lateral distribution of field-emitted electrons from a carbon nanofiber array: A theoretical calculation**

Stylianos Siontas, Andreas Kyritsakis, John P. Xanthakis, Stefano Iacobucci and Gianni Stefani  
J. Vac. Sci. Technol. B **32**, 02B107 (2014); <http://dx.doi.org/10.1116/1.4862237>

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**Effect of electron focusing in x-ray sources using LiTaO<sub>3</sub> crystals excited by neodymium-doped yttrium lithium fluoride laser light**

Kosuke Nakahama, Michiaki Takahashi, Satoshi Abo, Fujio Wakaya and Mikio Takai  
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## 30TH NORTH AMERICAN MOLECULAR BEAM EPITAXY CONFERENCE (30TH NAMBE 2013)

**Carrier lifetime studies in midwave infrared type-II InAs/GaSb strained layer superlattice**

Brianna Klein, Nutan Gautam, Elena Plis, Ted Schuler-Sandy, Thomas J. Rotter, Sanjay Krishna, Blair C. Connelly, Grace D. Metcalfe, Paul Shen and Michael Wraback  
J. Vac. Sci. Technol. B **32**, 02C101 (2014); <http://dx.doi.org/10.1116/1.4862085>

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**Closed-cycle cooling of cryopanels in molecular beam epitaxy**

Ryan B. Lewis, Vahid Bahrami-Yekta, Medhaj J. Patel, Thomas Tiedje and Mostafa Masnadi-Shirazi  
J. Vac. Sci. Technol. B **32**, 02C102 (2014); <http://dx.doi.org/10.1116/1.4862088>

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**Study of thermal stability of distributed Bragg reflectors based on epitaxial rare-earth oxide and silicon heterostructures**

Rytis Dargis, Jeffrey Leathersich, Andrew Clark and Erdem Arkun  
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## 30TH NORTH AMERICAN MOLECULAR BEAM EPITAXY CONFERENCE (30TH NAMBE 2013)

### InGaAs/GaAsSb based two-dimensional electron gases

Hermann Detz, Jonathan Silvano de Sousa, Horst Leonhardt, Pavel Klang, Tobias Zederbauer, Aaron Maxwell Andrews, Werner Schrenk, Jürgen Smoliner and Gottfried Strasser

J. Vac. Sci. Technol. B **32**, 02C104 (2014); <http://dx.doi.org/10.1116/1.4863299>

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### Near infrared intersubband absorption of CdSe/MgSe quantum wells grown on InP substrate with an InAlAs buffer layer

Guopeng Chen, Kuaile Zhao, Maria C. Tamargo and Aidong Shen

J. Vac. Sci. Technol. B **32**, 02C105 (2014); <http://dx.doi.org/10.1116/1.4863496>

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### Nanotemplate-directed InGaAs/GaAs single quantum dots: Toward addressable single photon emitter arrays

Jiefei Zhang, Zachary Lingley, Siyuan Lu and Anupam Madhukar

J. Vac. Sci. Technol. B **32**, 02C106 (2014); <http://dx.doi.org/10.1116/1.4863680>

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### Semiempirical method of suppressing interference effects in photoluminescence spectra of GaN heterostructures

Yu-Li Wang, Kuan-Yu Chen, Wei-Chen Yang, Shao-Yen Chiu and Keh-Yung Cheng

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### MBE growth of P-doped 1.3 $\mu\text{m}$ InAs quantum dot lasers on silicon

Alan Y. Liu, Chong Zhang, Andrew Snyder, Dmitri Lubyshev, Joel M. Fastenau, Amy W. K. Liu, Arthur C. Gossard and John E. Bowers

J. Vac. Sci. Technol. B **32**, 02C108 (2014); <http://dx.doi.org/10.1116/1.4864148>

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### Optimum growth window for InAs/GaInSb superlattice materials tailored for very long wavelength infrared detection

Heather J. Haugan, Gail J. Brown, Krishnamurthy Mahalingam, Larry Grazulis, Gary T. Noe, Nathan E. Ogden and Junichiro Kono

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### Effect of surface states on the electrical properties of MBE grown modulation doped AlGaAs/GaAs

Alejandro Cisneros-de-la-Rosa, Irving Eduardo Cortes-Mestizo, Esteban Cruz-Hernández, Víctor Hugo Méndez-García, Luis Zamora-Perezo, José Vulfrano González-Fernández, Raúl Balderas-Navarro, Andrei Yu. Gorbatchev and Máximo López-López

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### Selectively grown GaAs nanodisks on Si(100) by molecular beam epitaxy

Chia-Pu Chu, Shamsul Arafin, Guan Huang, Tianxiao Nie, Kang L. Wang, Yong Wang, Jin Zou, Syed M. Qasim and Mohammed S. BenSaleh

J. Vac. Sci. Technol. B **32**, 02C111 (2014); <http://dx.doi.org/10.1116/1.4865477>

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### AlGaN cladding-free 482 nm continuous wave nitride laser diodes grown by plasma-assisted molecular beam epitaxy

Czesław Skierbiszewski, Henryk Turski, Grzegorz Muziol, Paweł Wolny, Grzegorz Cywiński, Szymon Grzanka, Julita Smalc-Koziorowska, Marta Sawicka, Piotr Perlin, Zbig R. Wasilewski and Sylwester Porowski

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### Engineering the color rendering index of phosphor-free InGaN/(Al)GaN nanowire white light emitting diodes grown by molecular beam epitaxy

Ashfiqua T. Connie, Hieu P. T. Nguyen, Sharif M. Sadaf, Ishiang Shih and Zetian Mi

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### Study on the coalescence of dislocation-free GaN nanowires on Si and SiO<sub>x</sub>

Shizhao Fan, Songrui Zhao, Xuedong Liu and Zetian Mi

J. Vac. Sci. Technol. B **32**, 02C114 (2014); <http://dx.doi.org/10.1116/1.4865915>

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### Semipolar (2021) GaN laser diodes operating at 388 nm grown by plasma-assisted molecular beam epitaxy

Marta Sawicka, Grzegorz Muziol, Henryk Turski, Anna Feduniewicz-Żmuda, Marcin Kryśko, Szymon Grzanka, Ewa Grzanka, Julita Smalc-Koziorowska, Martin Albrecht, Robert Kucharski, Piotr Perlin and Czesław Skierbiszewski

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### High electron mobility in InSb epilayers and quantum wells grown with AlSb nucleation on Ge-on-insulator substrates

Mukul C. Debnath, Tetsuya D. Mishima, Michael B. Santos, Lucas C. Phinney, Terry D. Golding and Khalid Hossain

J. Vac. Sci. Technol. B **32**, 02C116 (2014); <http://dx.doi.org/10.1116/1.4866397>

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### Silicon nitride thin films deposited using electron-beam evaporation in an RF plasma MBE system

D. Scott Katzer, David J. Meyer, David F. Storm, Neeraj Nepal and Virginia D. Wheeler

J. Vac. Sci. Technol. B **32**, 02C117 (2014); <http://dx.doi.org/10.1116/1.4867435>

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**Orientation-dependent pseudomorphic growth of InAs for use in lattice-mismatched mid-infrared photonic structures**

Charles Meyer, Emily Cheng and Gregory Triplett

J. Vac. Sci. Technol. B **32**, 02C118 (2014); <http://dx.doi.org/10.1116/1.4867879>

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**Rapid thermal annealing effect on GaAsBi/GaAs single quantum wells grown by molecular beam epitaxy**

Perry C. Grant, Dongsheng Fan, Aboozar Mosleh, Shui-Qing Yu, Vitaliy G. Dorogan, Michael E. Hawkridge, Yuriy I. Mazur, Mourad Benamara, Gregory J. Salamo and Shane R. Johnson

J. Vac. Sci. Technol. B **32**, 02C119 (2014); <http://dx.doi.org/10.1116/1.4868110>

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**Molecular beam epitaxy using bismuth as a constituent in InAs and a surfactant in InAs/InAsSb superlattices**

Preston T. Webster, Nathaniel A. Riordan, Chaturvedi Gogineni, Shi Liu, Jing Lu, Xin-Hao Zhao, David J. Smith, Yong-Hang Zhang and Shane R. Johnson

J. Vac. Sci. Technol. B **32**, 02C120 (2014); <http://dx.doi.org/10.1116/1.4868111>

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**Studying the formation of nitrogen δ-doped layers on GaAs(001) using reflection high-energy electron diffraction**

Norihisa Nishimoto, Masahiko Kondow and Fumitaro Ishikawa

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